

AMENDMENTS TO THE CLAIMS

Claim 1 (Currently Amended): A nitride semiconductor light emitting diode comprising:

an active layer comprising of a nitride semiconductor; and

a reflecting mirror separated by a distance of approximately $(k \cdot \lambda/2 + \lambda/4)/n$ from a center of the active layer, ~~wherein~~ where

λ is the wavelength of light projected from the active layer,

n is the mean refractive index of an area between the active layer and the reflecting mirror, and

k is an integer.

Claim 2 (Original): A nitride semiconductor light emitting diode as set forth in Claim 1, wherein the reflecting mirror is also an electrode for supplying electric current to the active layer.

Claim 3 (Currently Amended): A nitride semiconductor light emitting diode as set forth in Claim 1, further comprising a convex lens ~~formed at~~ on a side of the active layer opposite the reflecting mirror ~~of the active layer~~.

Claim 4 (Currently Amended): A nitride semiconductor light emitting diode comprising:

a substrate;

an active layer comprising ~~of~~ a nitride semiconductor ~~and being grown~~ on the substrate; and

a reflecting mirror laminated above the active layer, the reflecting mirror being separated by a distance of approximately $(k \cdot \lambda/2 + \lambda/4)/n$ from a center of the active layer, ~~wherein~~ where

λ is the wavelength of light projected from the active layer,

n is the mean refractive index of an area between the active layer and the reflecting mirror, and

k is an integer.

Claim 5 (Currently Amended): A nitride semiconductor light emitting diode comprising:

a substrate;

a nitride semiconductor ~~grown~~ on the substrate ~~;~~ ~~the~~ ,

where the nitride semiconductor being is thick at a central portion thereof and thin at a peripheral portion thereof, and ~~having~~

where the nitride semiconductor has an active layer being formed in the thick central portion thereof;

a first electrode ~~being formed in~~ on an upper face of the thick central portion; and

a second electrode ~~being formed in~~ on an upper face of the thin peripheral portion, wherein,

when viewed from a direction perpendicular to the substrate,

the second electrode surrounds the first electrode; and

the outer circumference of the first electrode is similar to at least one of the inner circumference and the outer circumference of the second electrode.

Claim 6 (Canceled)

Claim 7 (Currently Amended): A nitride semiconductor light emitting diode as set forth in Claim 5, wherein a center of the first electrode and a center of the second electrode are positioned such that one is above the other if when viewed from a direction perpendicular to the substrate.

Claim 8 (Original): A nitride semiconductor light emitting diode as set forth in Claim 5, wherein the profile of at least one of the first electrode and the second electrode forms a smooth continuum and contains no corners.

Claim 9 (Currently Amended): A nitride semiconductor light emitting diode ~~as set forth in Claim 5, wherein the~~ comprising:

a substrate;

a nitride semiconductor on the substrate,

where the nitride semiconductor is thick at a central portion thereof and thin at a peripheral portion thereof, and

where the nitride semiconductor has an active layer in the thick central portion thereof;

a first electrode on an upper face of the thick central portion; and

a second electrode on an upper face of the thin peripheral portion, wherein

the nitride semiconductor light emitting diode further comprises a reflecting mirror is
formed above the active layer of the thick central portion, the reflecting mirror being separated by a distance of approximately $(k \cdot \lambda/2 + \lambda/4)/n$ from a center of the active layer,
~~wherein~~ where

λ is the wavelength of light projected from the active layer,

n is the mean refractive index of an area between the active layer and the reflecting mirror, and

k is an integer.

Claim 10 (New): A nitride semiconductor light emitting diode as set forth in Claim 7, wherein the center of the first electrode and the center of the second electrode are positioned such that one is directly above the other when viewed from a direction perpendicular to the substrate.

Claim 11 (New): A nitride semiconductor light emitting diode as set forth in Claim 5, wherein the outer circumference of the first electrode has a polygonal shape.

Claim 12 (New): A nitride semiconductor light emitting diode as set forth in Claim 5, wherein the outer circumference of the first electrode has a circular shape and at least one of the inner circumference and the outer circumference of the second electrode has a circular shape.